/ Descriptions

SOT-23 N MOS N- CHANNEL MOSFET in a SOT-23 Plastic Package.

/ Features

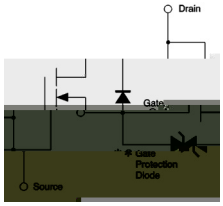
, , , 500V HBM

Low on-resistance, fast switching speed, low voltage drive, easily designed drive circuits, easy to parallel. ESD protected up to 500V HBM .

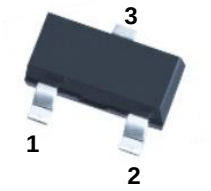
/ Applications

Interfacing, switching.

/ Equivalent Circuit



/ Pinning



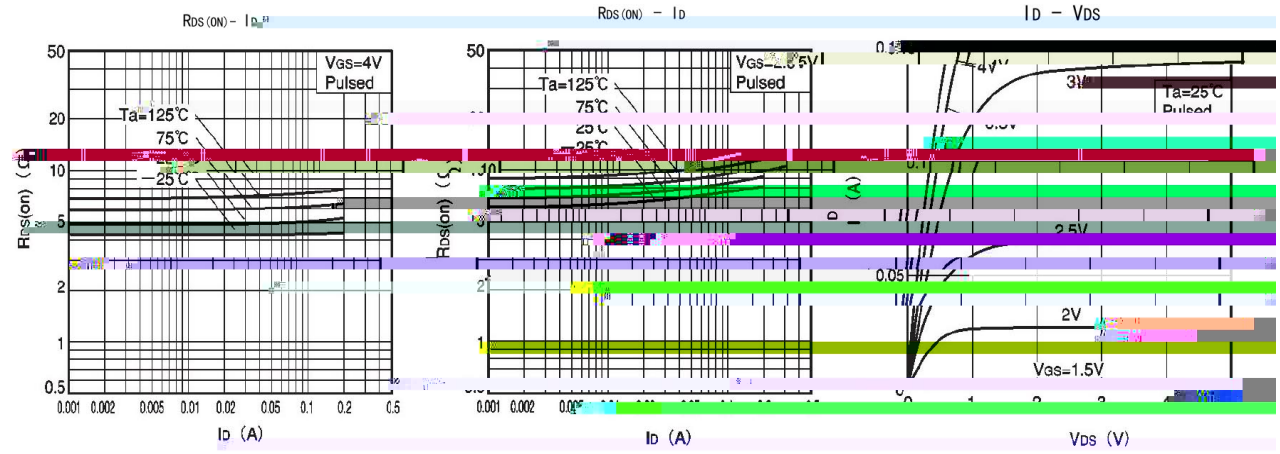
PIN1 G PIN 2 S PIN 3 D

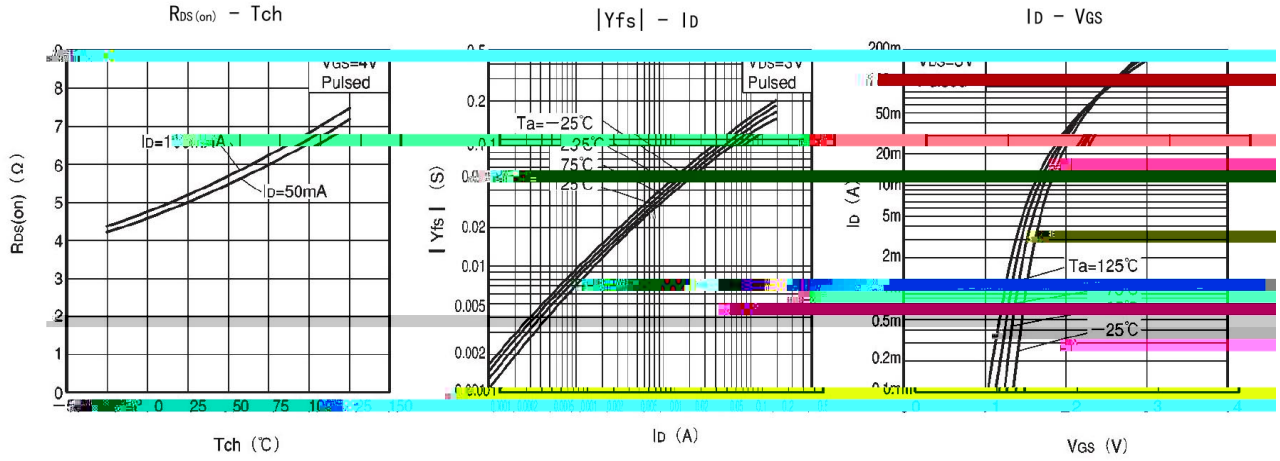
/ Marking

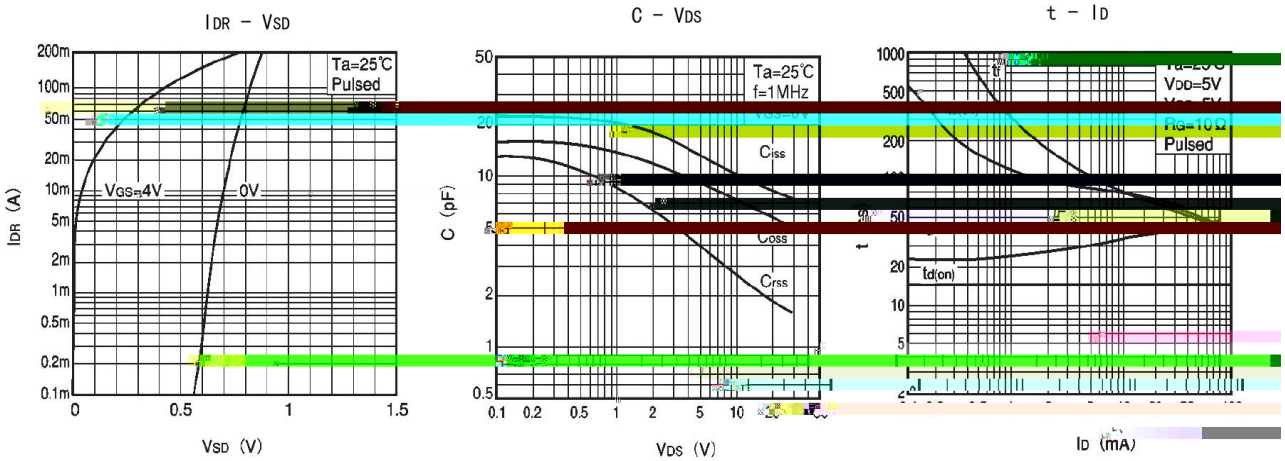
Marking	KL

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	±20	V
Drain Current – Continuous	I_D	100	mA
Drain Current- Pulsed	I_{DP} *1	400	mA
Reverse Drain Current – Continuous	I_{DR}	100	mA
Reverse Drain Current –Pulsed	I_{DRP} *1	200	mA
Total Power Dissipation	P_D *2		

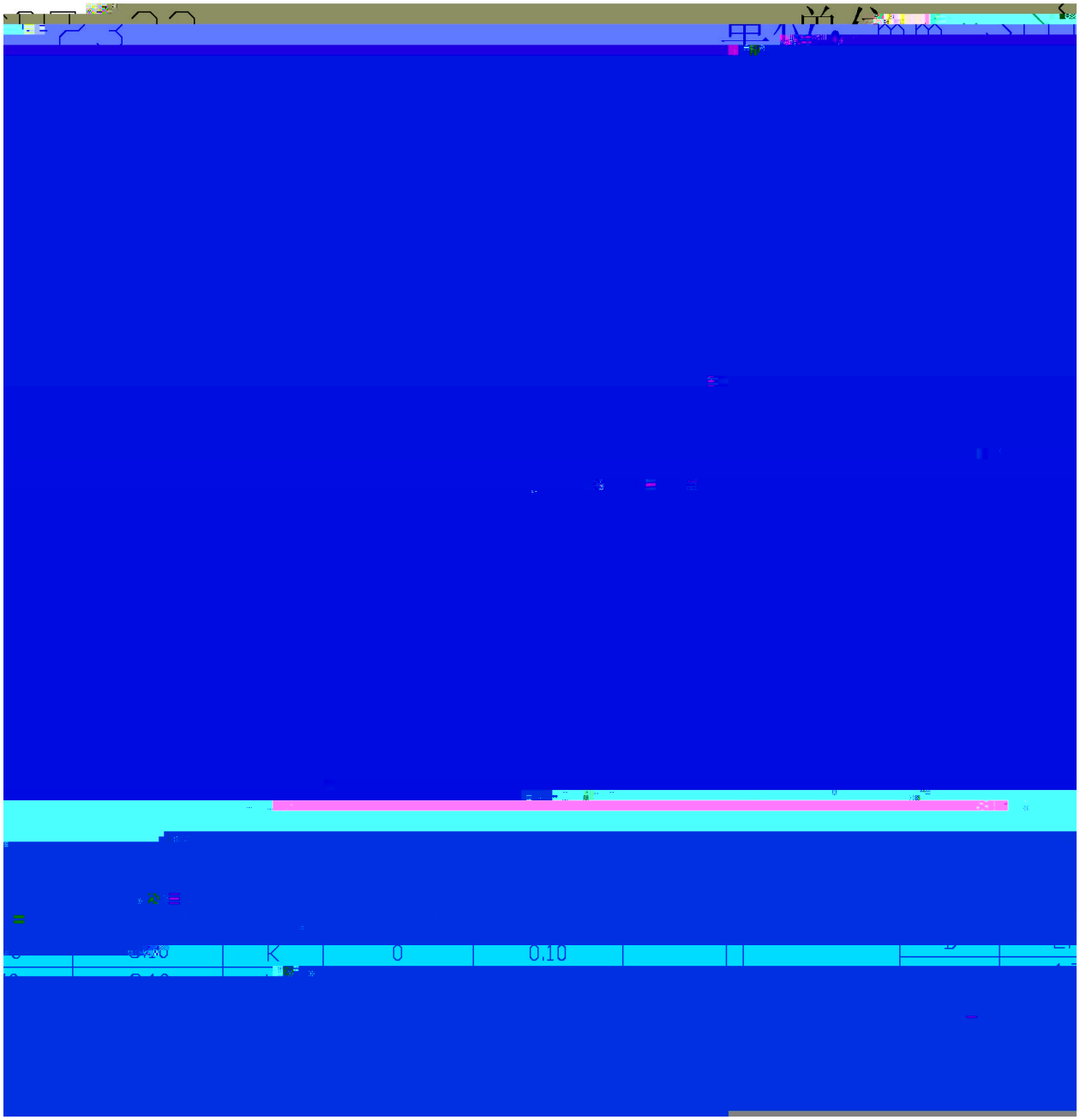
/ Electrical Characteristic Curve



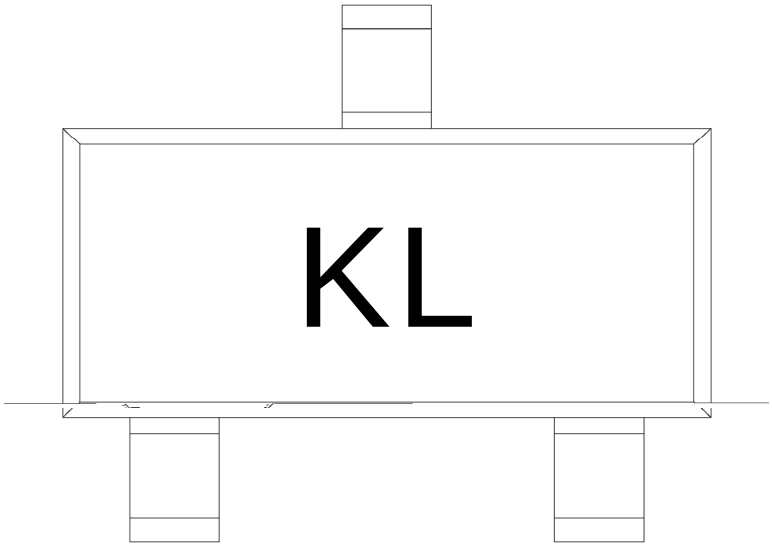




/ Package Dimensions



/ Marking Instructions

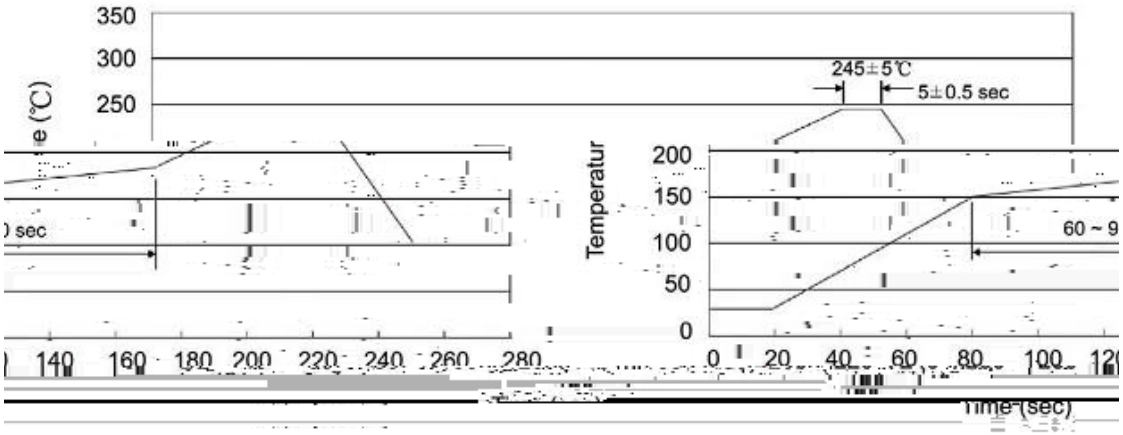


KL:

Note:

KL	Package Type

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

1 150 180 60 90sec;
2 245±5 5±0.5sec;
3 2 10 /sec.

1.Preheating:150~180 , Time:60~90sec.
2.Peak Temp.:245±5 , Duration:5±0.5sec.
3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-23	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205

/ Notices